

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled)
2. (Currently Amended) A semiconductor device comprising:
 - a first wiring and a second wiring formed of a first conductive film on an insulating surface;
 - a second conductive film formed on the first and second wirings so as to correspond thereto;
 - a pair of first semiconductor films of one conductivity type formed on the second conductive film;
 - a second semiconductor film formed on and extending between the pair of first semiconductor films;
 - an insulating film formed on the second semiconductor film; [[and]]
 - a third conductive film formed on the insulating film[[,]]; and
 - a storage capacitor comprising:
 - a first layer comprising a same material as the first conductive film and the second wiring on the insulating surface;
 - a second layer comprising a same material as the second conductive film on the first layer;
 - a third layer comprising a same material as the pair of first semiconductor films of one conductivity type on the second layer;
 - a fourth layer comprising a same material as the second semiconductor film on the second layer;

a fifth layer comprising a same material as the insulating film on the fourth layer; and

a sixth layer comprising a same material as the third conductive film on the fifth layer;

wherein an end portion of the second semiconductor film is provided inside an end portion of the second conductive film, and

wherein each of the first wiring and the second wiring has tapered inner and outer edges.

3. (Canceled)

4. (Currently Amended) A semiconductor device comprising:

a data wiring and a pixel electrode formed on an insulating surface;

barrier metal formed so as to correspond to the data wiring and the pixel electrode;

a pair of first semiconductor films of one conductivity type formed on the barrier metal;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

a gate insulating film formed on the second semiconductor film; [[and]]

a gate electrode formed on the gate insulating film[[,]]; and

a storage capacitor comprising:

a first layer comprising a same material as the pixel electrode on the insulating surface;

a second layer comprising a same material as the barrier metal on the first layer;

a third layer comprising a same material as the pair of first semiconductor films of one conductivity type on the second layer;

a fourth layer comprising a same material as the second semiconductor film on the second layer;

a fifth layer comprising a same material as the gate insulating film on the fourth layer; and

a sixth layer comprising a same material as the gate electrode on the fifth layer;

wherein an end portion of the second semiconductor film is provided inside an end portion of the barrier metal, and

wherein each of the data wiring and the pixel electrode has tapered inner and outer edges.

5.-20. (Canceled)

21. (Original) A semiconductor device according to claim 2, wherein each of the first wiring and the second wiring comprises aluminum.

22. (Original) A semiconductor device according to claim 2, wherein each of the first wiring and the second wiring comprises a conductive oxide film.

23. (Previously Presented) A semiconductor device according to claim 2, wherein the third conductive film comprises at least one material selected from the group consisting of Ta, Ti, W and an alloy thereof.

24. (Original) A semiconductor device according to claim 2, wherein the semiconductor device is one selected from the group consisting of a mobile phone, a video camera, a portable information terminal, a liquid crystal TV receiver, a portable book, a personal computer, a DVD player, and a digital still camera.

25. (Canceled)

26. (Original) A semiconductor device according to claim 4, wherein each of the data wiring and the pixel electrode comprises aluminum.

27. (Original) A semiconductor device according to claim 4, wherein each of the data wiring and the pixel electrode comprises a conductive oxide film.

28. (Previously Presented) A semiconductor device according to claim 4, wherein the gate electrode comprises at least one material selected from the group consisting of Ta, Ti, W, and an alloy thereof.

29. (Original) A semiconductor device according to claim 4, wherein the semiconductor device is one selected from the group consisting of a mobile phone, a video camera, a portable information terminal, a liquid crystal TV receiver, a portable book, a personal computer, a DVD player, and a digital still camera.

30. (Currently Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; [[and]]

a third conductive film including a gate electrode formed on the insulating film[.];

and

a storage capacitor comprising:

a first layer comprising a same material as the at least first and second conductive films on the insulating surface;

a second layer comprising a same material as the pair of first semiconductor films over the first layer;

a third layer comprising a same material as the second semiconductor film on the second layer;

a fourth layer comprising a same material as the insulating film on the third insulating layer; and

a fifth layer comprising a same material as the third conductive film on the fourth layer.

wherein each of the first and second conductive films and the pair of first semiconductor films has tapered inner and outer edges.

31. (Currently Amended) The semiconductor device according to claim 30 wherein the edge of the pair of first semiconductor films has a tapered angle of 5-45°.

32. (Previously Presented) The semiconductor device according to claim 30 further comprising a barrier metal layer interposed between the first and second conductive films and the pair of first semiconductor films, respectively, wherein said barrier metal layer comprises a material selected from the group consisting of Ti, Ta, TiN and TaN.

33. (Previously Presented) The semiconductor device according to claim 30 wherein said third conductive film has a tapered outer edge.

34. (Currently Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; [[and]]

a third conductive film including a gate electrode formed on the insulating film[[,]]; and

a storage capacitor comprising:

a first layer comprising a same material as one of the at least first and second conductive films on the insulating surface;

a second layer comprising a same material as the pair of first semiconductor films over the first layer;

a third layer comprising a same material as the second semiconductor film on the second layer; and

a fourth layer comprising a same material as the third conductive film,

wherein each of the pair of first semiconductor films and the second semiconductor film has tapered inner and outer edges and the pair of first semiconductor films extend beyond side edges of the second semiconductor film.

35. (Previously Presented) The semiconductor device according to claim 34 wherein the edge of the pair of first semiconductor films has a tapered angle of 5-45°.

36. (Previously Presented) The semiconductor device according to claim 34 further comprising a barrier metal layer interposed between the first and second conductive films and the pair of first semiconductor films, respectively, wherein said

barrier metal layer comprises a material selected from the group consisting of Ti, Ta, TiN and TaN.

37. (Currently Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; [[and]]

a third conductive film including a gate electrode formed on the insulating film[.];
and

a storage capacitor comprising:

a first layer comprising a same material as one of the at least first and second conductive films on the insulating surface;

a second layer comprising a same material as the pair of first semiconductor films over the first layer;

a third layer comprising a same material as the second semiconductor film on the second layer;

a fourth layer comprising a same material as the insulating film on the third layer; and

a fifth layer comprising a same material as the third conductive film on the fourth layer.

wherein each of the second semiconductor film and the third conductive film has tapered inner and outer edges and the second semiconductor film extends beyond side edges of the third conductive film.

38. (Previously Presented) The semiconductor device according to claim 37 wherein the edge of the third conductive film has a tapered angle of 15-45°.

39. (Previously Presented) The semiconductor device according to claim 37 further comprising a barrier metal layer interposed between the first and second conductive films and the pair of first semiconductor films, respectively, wherein said barrier metal layer comprises a material selected from the group consisting of Ti, Ta, TiN and TaN.

40. (Currently Amended) A semiconductor device comprising:
at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;
a pair of barrier metal layers formed on the first and second conductive films wherein said barrier metal layers have a tapered outer edge;
a pair of first semiconductor films of one conductivity type formed on the pair of barrier metal layers, respectively, wherein each of the pair of first semiconductor films has a tapered outer edge;
a second semiconductor film formed on and extending between the pair of first semiconductor films wherein the second semiconductor film has a tapered outer edge;
an insulating film including a gate insulating film formed on the second semiconductor film; [[and]]
a third conductive film including a gate electrode formed on the insulating film wherein said third conductive film has a tapered outer edge[[,]]; and
a storage capacitor comprising:
a first layer comprising a same material as one of the at least first and second conductive films on the insulating surface;

a second layer comprising a same material as the pair of barrier metal layers on the first layer;

a third layer comprising a same material as the pair of first semiconductor films on the second layer;

a fourth layer comprising a same material as the second semiconductor film on the third layer;

a fifth layer comprising a same material as the insulating film on the fourth layer;
and

a sixth layer comprising a same material as the third conductive film on the fifth layer.

wherein said insulating film extends beyond the outer edge of the third conductive film, and said second semiconductor film extends beyond the outer edge of the insulating film,

wherein each of the first conductive film and the second conductive film has tapered inner and outer edges.

41. (Previously Presented) The semiconductor device according to claim 40 wherein the edge of the third conductive film has a tapered angle of 15-45°.

42. (Previously Presented) The semiconductor device according to claim 40, wherein said pair of barrier metal layers comprises a material selected from the group consisting of Ti, Ta, TiN and TaN.